The ICSI-7 will provide a unique forum for reviewing and discussing novel developments in physics and device technologies of Si epitaxy, heterostructures, and nanostructures. The conference is a biannual succession of the previous ICSI conferences (1st: Miyagi Zao, Japan, 1999; 2nd: Strasbourg, France, 2001; 3rd: Santa Fe, USA, 2003; 4th: Awaji Island, Japan, 2005; 5th: Marseille, France, 2007; 6th: Los Angeles, USA, 2009).

NOTE: 6th Int. Symp. on Control of Semiconductor Interfaces (ICSI-VI, May 25(Wed)-27(Fri), 2011) & some workshops will be held successively. Some focus sessions will be joint with ICSI-VI.

CONFERENCE TOPICS

- Growth, Characterization and Modeling of Si and Group IV (C, Si, Ge, Sn) based Thin Film Materials including research on various interfaces on Si;
- Formation and Characterization of Group IV based Nanostructures including quantum dots, nanowires and self-assembly processes;
- Process Technologies for Group IV based Heterostructures including doping,
- Source/drain and channel engineering as well as strained Si;
- Electronic Properties and Device Applications such as transistors and nano-structured devices;
- Optical Properties and Device Applications including solar cells of Si and Ge based heterostructures;
- Germanium based semiconductor... from materials to devices;
- Si(Si)-based materials growth and device fabrication for spintronics such as spin polarized electron injection, transport, and manipulation, as well as other electron spin based phenomena;
- Growth, characterization and applications of epitaxial (high-k) dielectric materials;
- Emerging technologies: Hetero-Epitaxial film growths on SiGe and characterization (Graphene, III-V and others materials).

The Organizers welcome you to ICSI-7 at Sendai, Japan.

Shigeaki Zaima (Chair)  Junichi Murota (Vice Chair)  Seiichi Miyazaki (Vice Chair)
Nagoya University, Japan  Tohoku University, Japan  Nagoya University, Japan

ABSTRACT SUBMISSION  
Deadline : FEBRUARY 15, 2011 (Extended)

PDF or MS Word file of Camera-ready two-page abstract (one-page main text and one-page figures), written in English on white bond paper (A4 size; 2.5cm margin on four sides), should be prepared. We will announce later how to submit the abstract on this web site. The abstract is strongly recommended to be prepared in Black/White. (Abstracts will be published in Black/White). The abstract should be headed by the title, author(s), affiliation(s), address, telephone number, fax number and e-mail address, and clearly describe the originality and new contributions of the work. Proceedings will be published in the special issue of Thin Solid Films (manuscript submission deadline will be around middle of May, 2011). Detailed information will be announced on the above symposium web site.

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